

### 2N4410



### **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 50 mA. Sourced from Process 16. See 2N5551 for characteristics.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	80	V	
V <sub>CBO</sub>	Collector-Base Voltage	120	V	
$V_{EBO}$	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	200	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

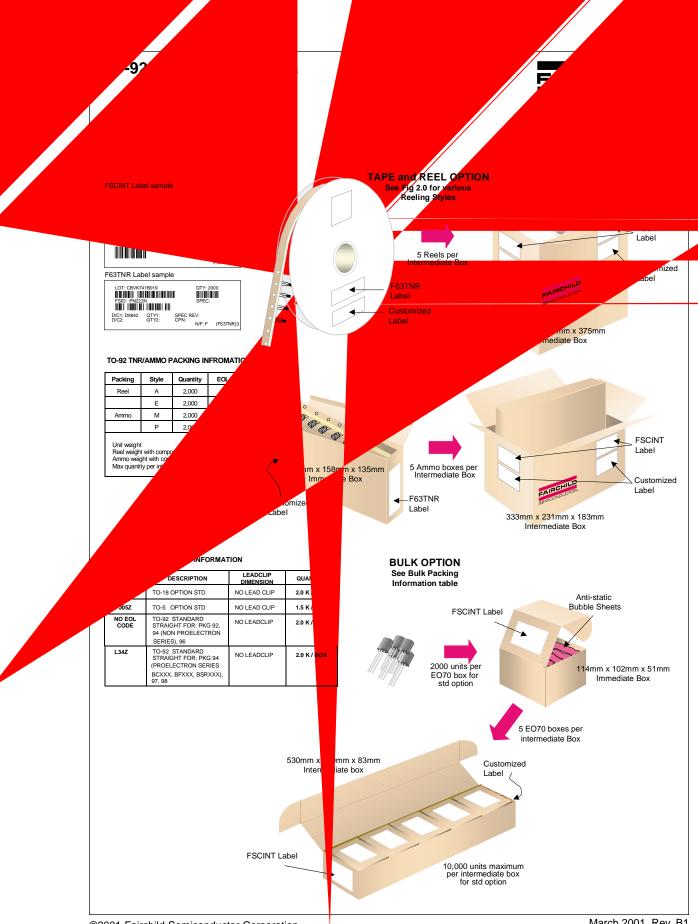
TA = 25°C unless otherwise noted

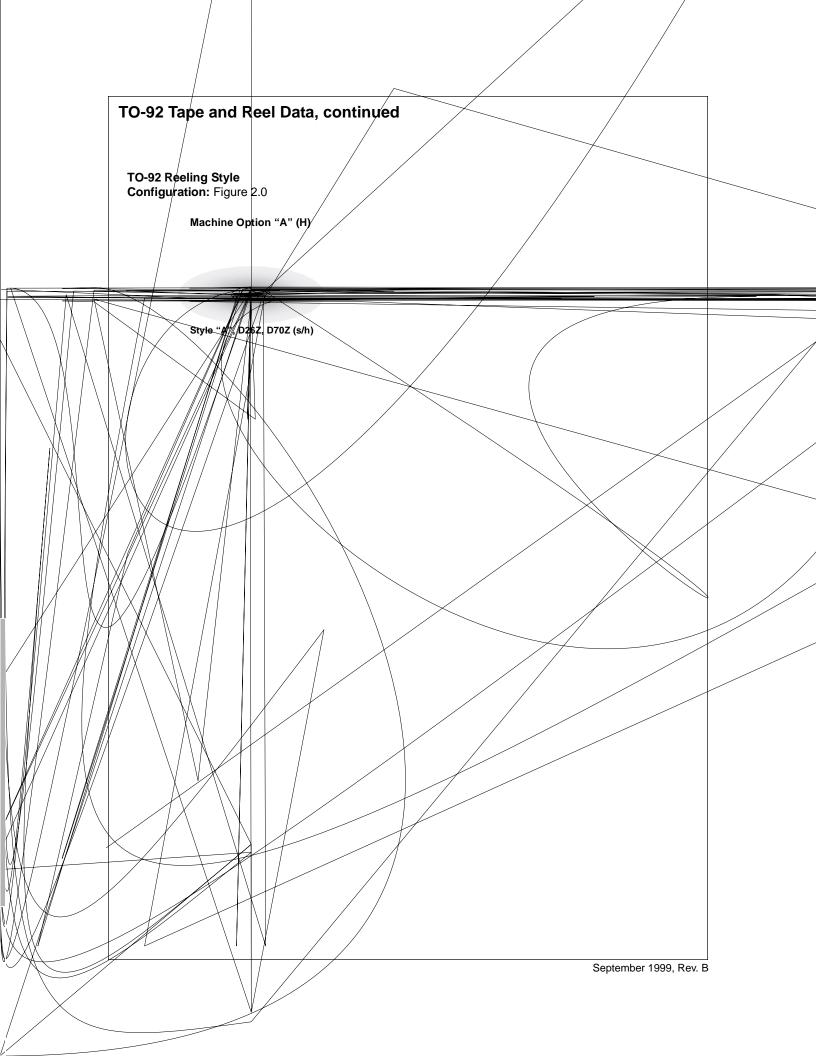
Symbol	Characteristic	Max	Units
		2N4410	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# NPN General Purpose Amplifier (continued)

Electr	Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units	
					•	
	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	80		V	
$V_{(BR)CEX}$	Collector-Emitter Breakdown Voltage	$I_C = 500 \mu A, V_{BB} = 5.0 \text{ V}$ $R_{BE} = 8.2 \text{ k}\Omega$	120		V	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A},  I_E = 0$	120		V	
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0, T <sub>A</sub> = 100 °C	10 1.0		nA μA	
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$	100		nA	
ON CHAR	RACTERISTICS*  DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	60 60	400		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$	- 00	0.2	V	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$		0.8	V	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$		0.8	V	
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	V <sub>CB</sub> = 10 V, f = 100 kHz		12	pF	
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> = 0.5 V, f = 100 kHz		50	pF	
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 30 MHz	2.0	10		

<sup>\*</sup>Pulse Test: Pulse Width



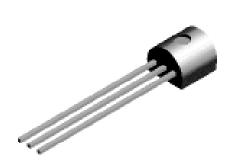


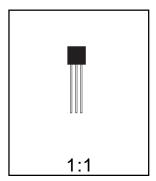


### **TO-92 Package Dimensions**



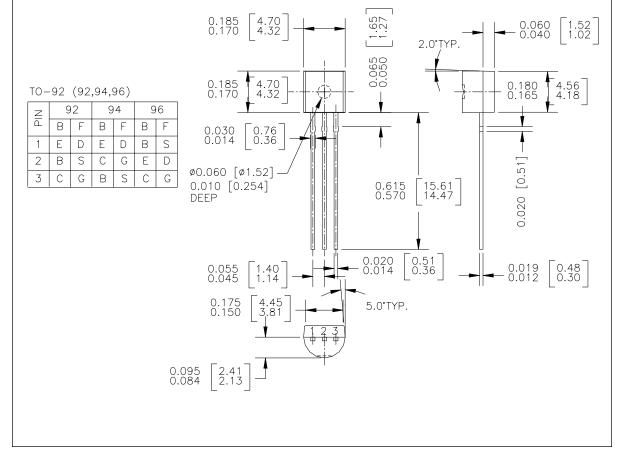
## TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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